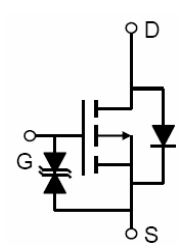



P-Channel Trench MOSFET

<p>Description</p> <p>The G12P10K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.</p> <p>General Features</p> <ul style="list-style-type: none"> ● V_{DS} -100V ● I_D (at $V_{GS} = -10V$) -12A ● $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 200 mΩ ● 100% Avalanche Tested ● RoHS Compliant ● ESD protection <p>Application</p> <ul style="list-style-type: none"> ● Power switch ● DC/DC converters 		 <p>Schematic diagram</p>  <p>TO-252</p>	
Device	Package	Marking	Packaging
G12P10K	TO-252	G12P10	2500pcs/Reel

Absolute Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise noted)			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-12	A
Drain Current-Continuous($T_C=100^{\circ}C$)	$I_D(100^{\circ}C)$	-9.2	A
Pulsed Drain Current	I_{DM}	-52	A
Single pulse avalanche energy ^(Note 5)	E_{AS}	65	mJ
Maximum Power Dissipation	P_D	40	W
Derating factor		0.32	W/ $^{\circ}C$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta Jc}$	3.13	$^{\circ}C/W$

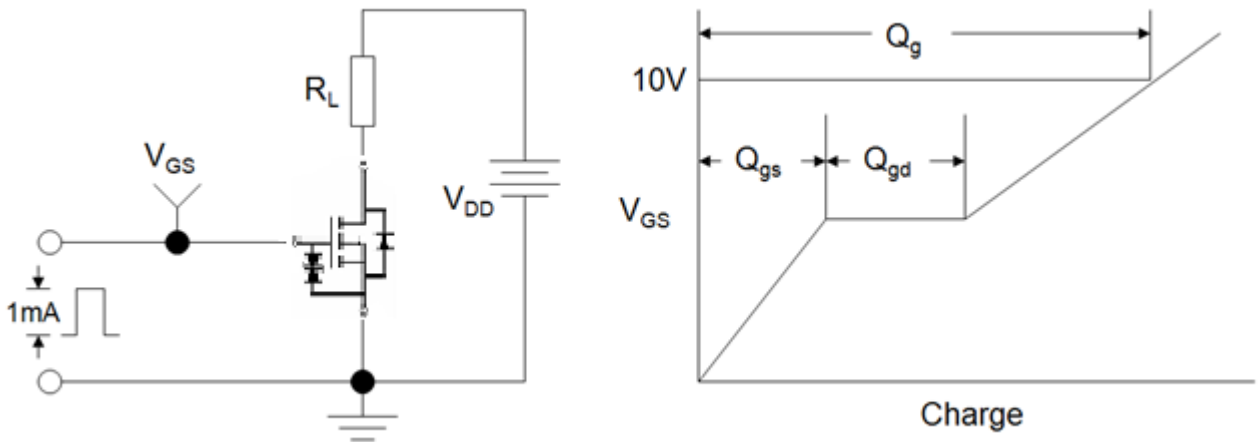
Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-100V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 10	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.9	-3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-6A$	-	170	200	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-15V, I_D=-5A$	12	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	760	-	pF
Output Capacitance	C_{oss}		-	260	-	pF
Reverse Transfer Capacitance	C_{rss}		-	170	-	pF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-50V, I_D=-10A$ $V_{GS}=-10V, R_{GEN}=9.1\Omega$	-	14	-	nS
Turn-on Rise Time	t_r		-	18	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	t_f		-	18	-	nS
Total Gate Charge	Q_g	$V_{DS}=-50V, I_D=-10A,$ $V_{GS}=-10V$	-	25	-	nC
Gate-Source Charge	Q_{gs}		-	5	-	nC
Gate-Drain Charge	Q_{gd}		-	7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-10A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S	-	-	-	-13	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ\text{C}, I_F = -10A$	-	35	-	nS
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A/\mu s$ (Note 3)	-	46	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

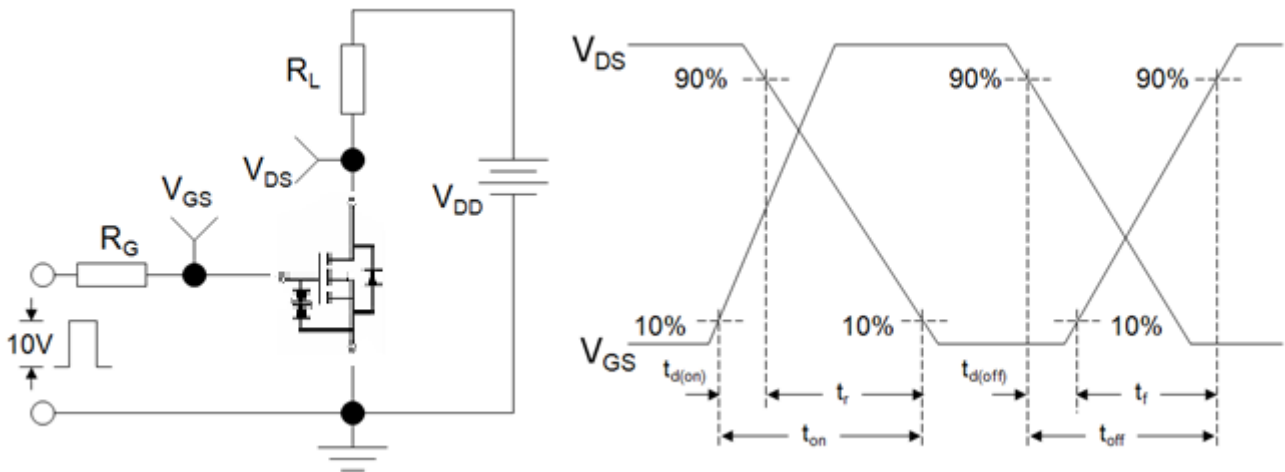
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $T_J=25^\circ\text{C}, V_{DD}=-50V, V_G=-10V, L=0.5\text{mH}, R_g=25\Omega$

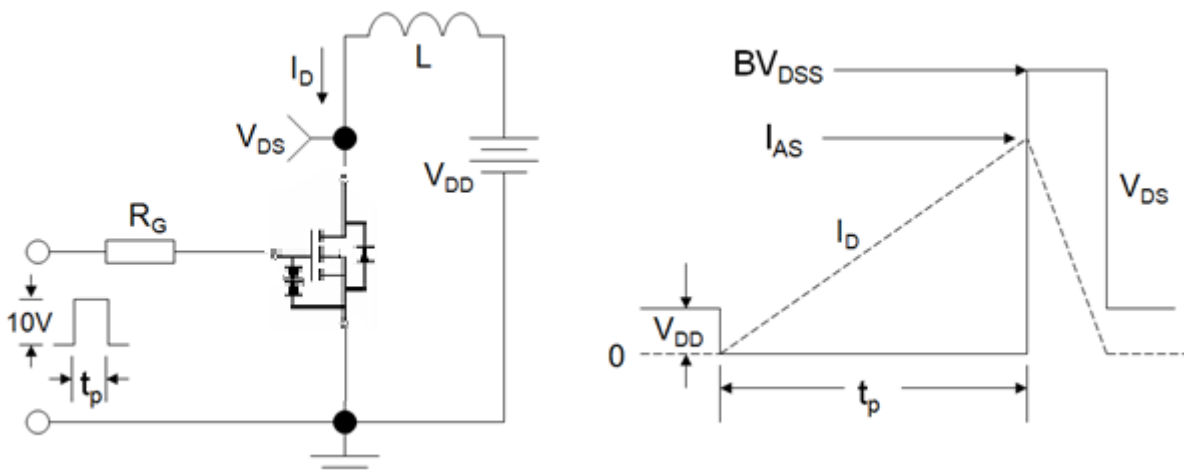
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

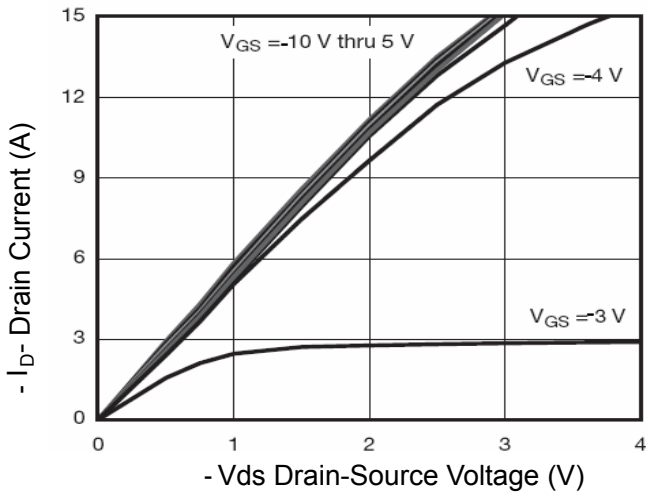


Figure 1 Output Characteristics

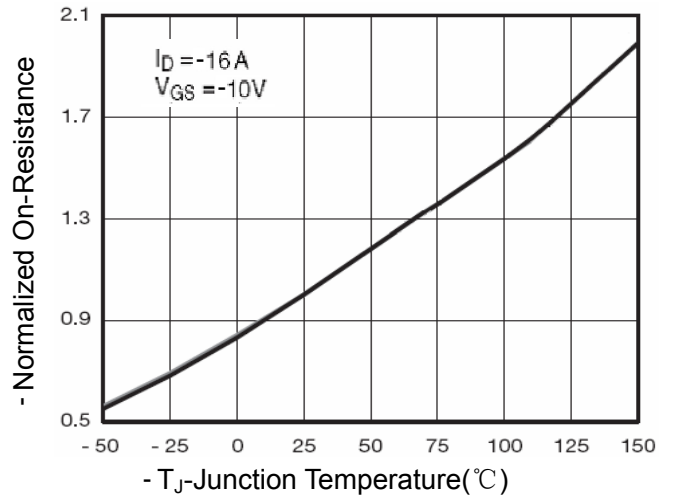


Figure 4 R_{dson} -Junction Temperature

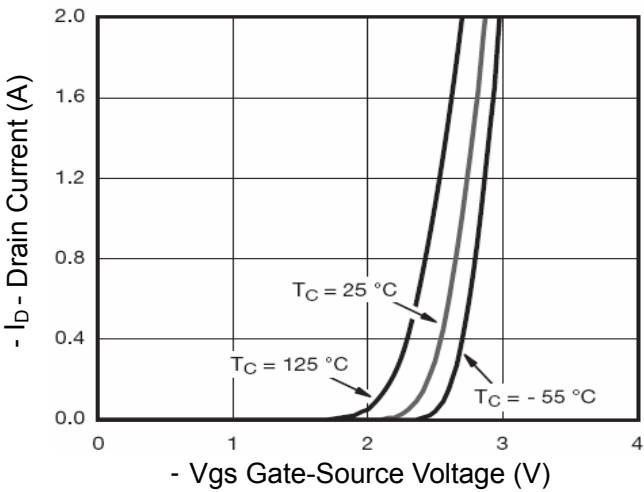


Figure 2 Transfer Characteristics

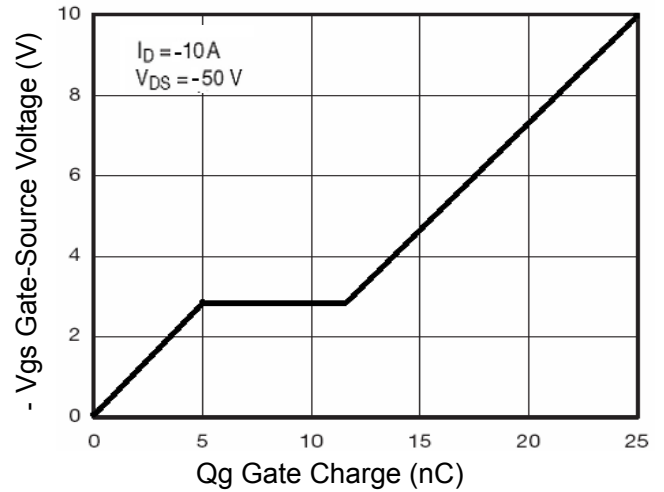


Figure 5 Gate Charge

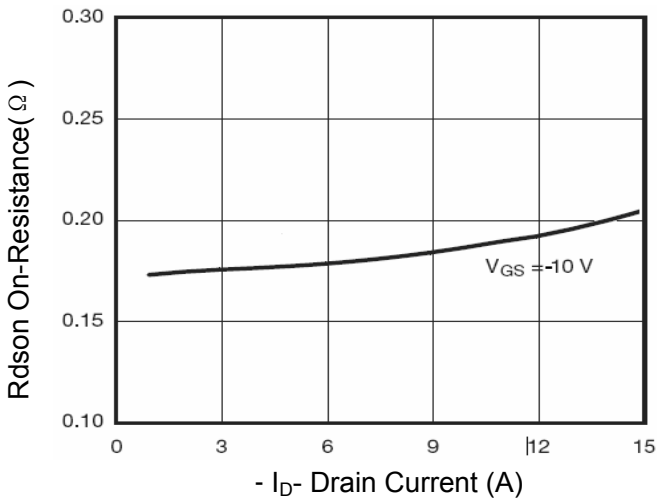


Figure 3 R_{dson} - Drain Current

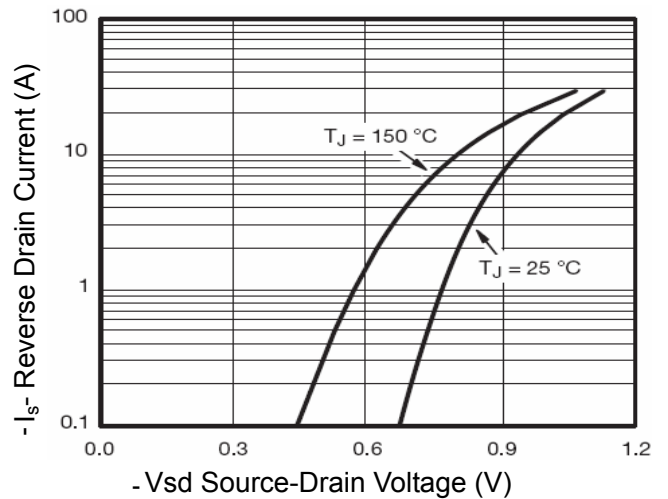


Figure 6 Source- Drain Diode Forward

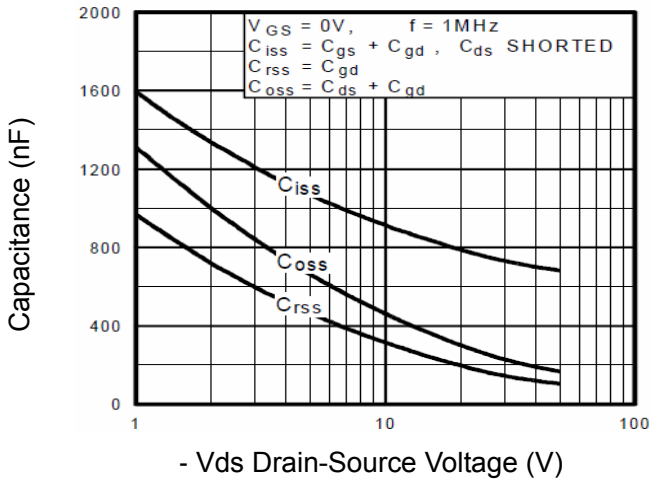


Figure 7 Capacitance vs Vds

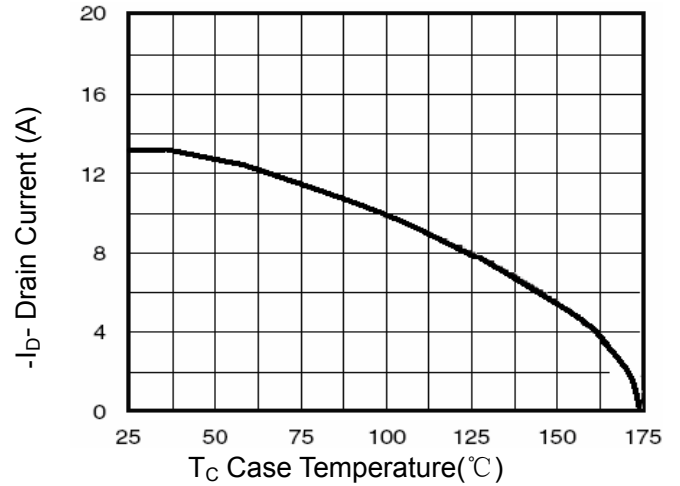


Figure 9 Drain Current vs Case Temperature

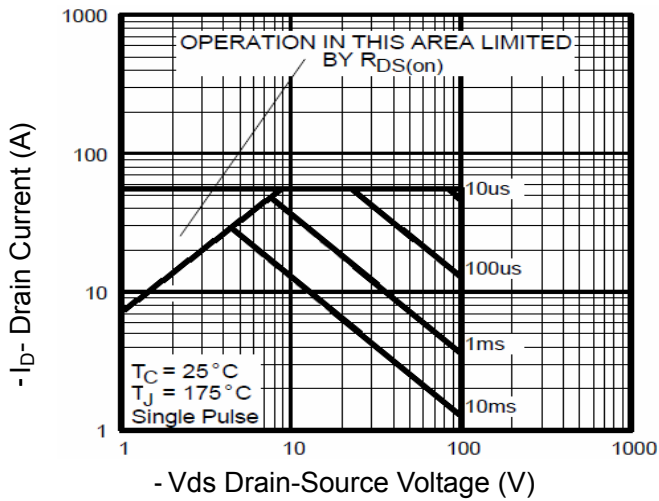


Figure 8 Safe Operation Area

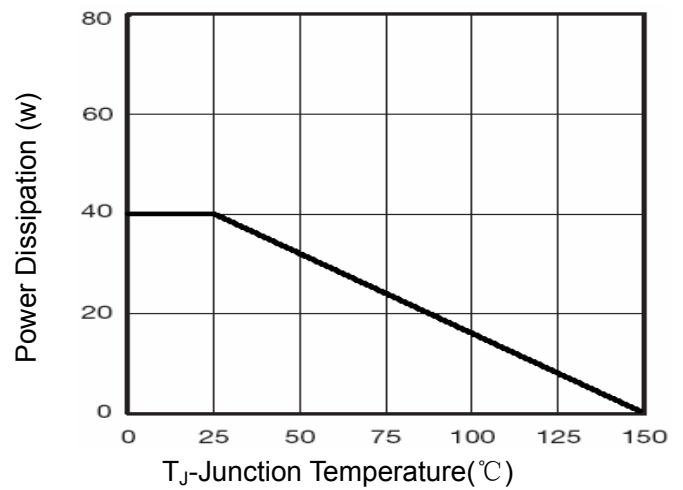


Figure 10 Power De-rating

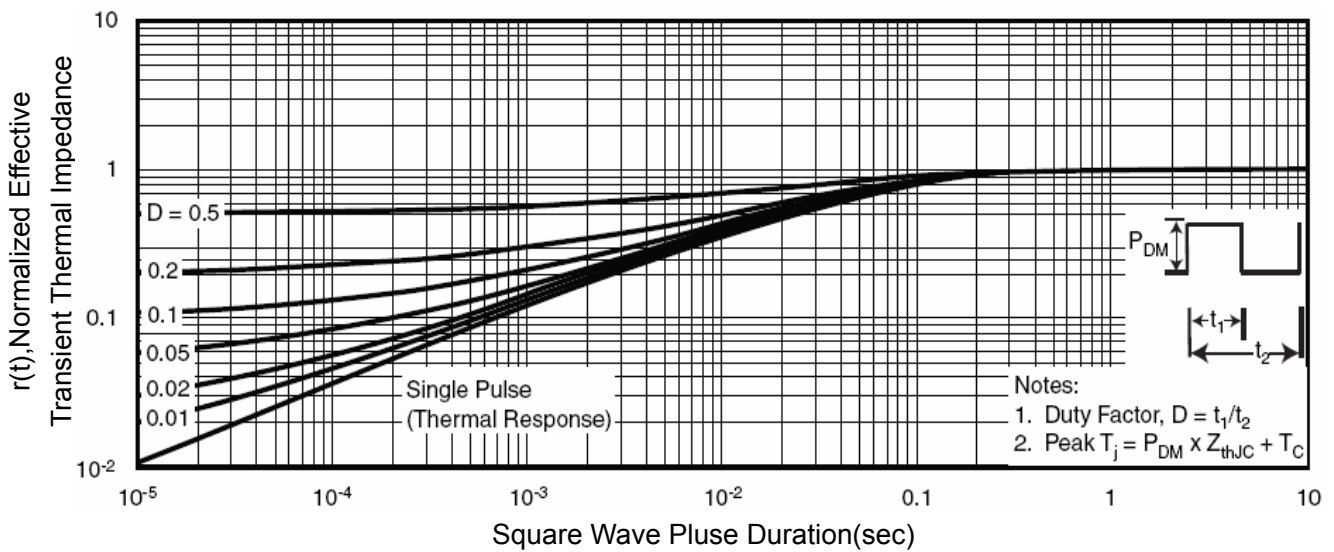
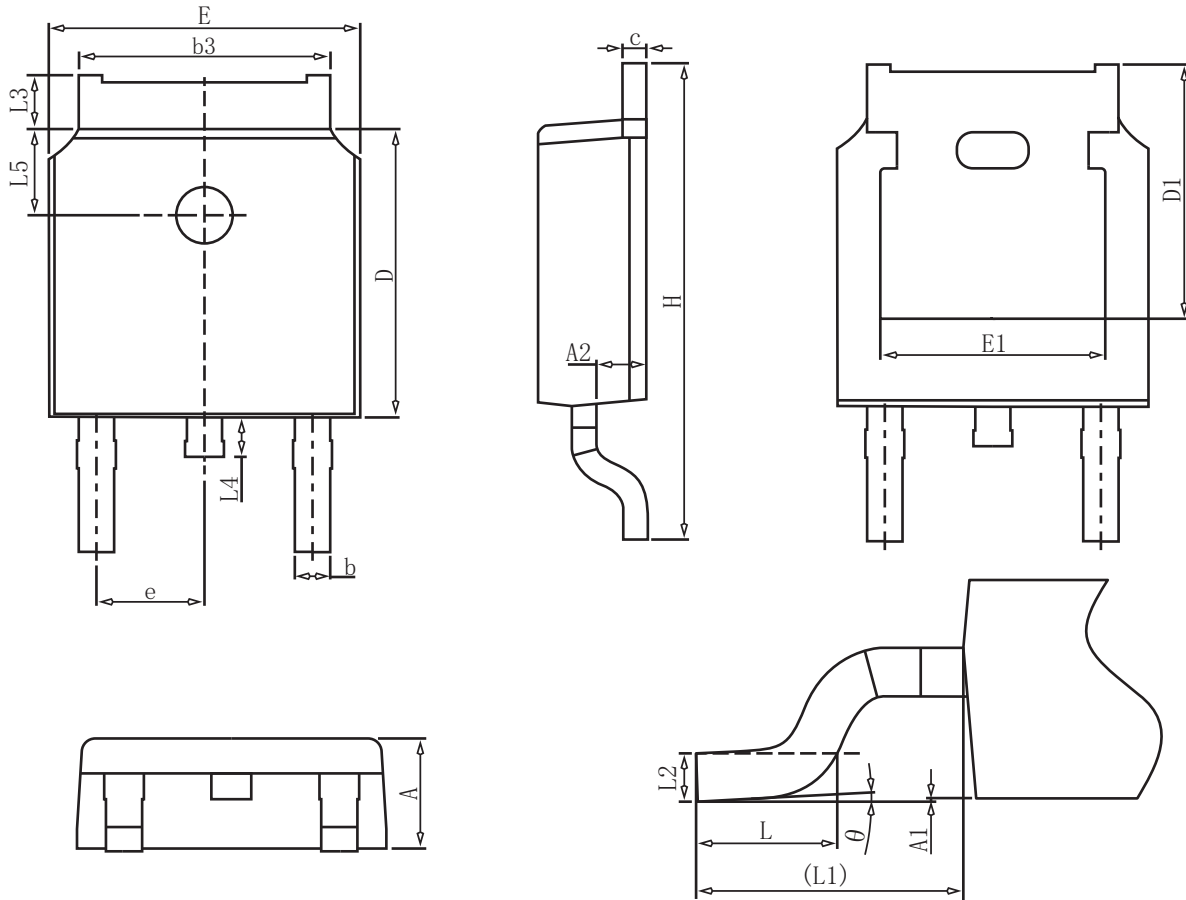


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90REF		
L2	0.51BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
theta	0°	-	8°